### Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

# **Panasonic**

MOS FET FCAB21830L

### FCAB21830L

## Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

#### ■ Features

- Source-source On-state Resistance : RSS(on) typ. = 2.5 m $\Omega$  ( VGS = 3.8 V )
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)

■ Marking Symbol : W6

#### Packaging

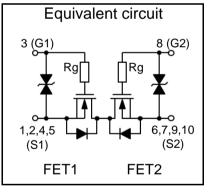
Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Demonstration	0	Datina	1.1		
<u>Parameter</u>	Symbol	Rating	Unit		
Source-source Voltage		VSS	12	V	
Gate-source Voltage		VGS	±8	V	
		IS <sup>*1</sup>	12.4	Α	
Source Current	DC	IS *2	22		
Source Current		IS <sup>*3</sup>	31	_ ^	
	Pulsed *4	ISp	124		
	DC	PD *1	0.51	W	
Total Power Dissipation		PD *2	1.7		
		PD *3	3.2		
Channel Temperature	Tch	150	°C		
Storage Temperature Range	Tstg	-55 to +150	°C		

### ■ Thermal Characteristics Ta = 25 °C

Parameter	Symbol	Rating	Unit	
	Rth *1	245		
Thermal Resistance (ch-a)	Rth *2	74	°C / W	
	Rth *3	39		



- Note \*1 Mounted on FR4 board (  $25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$  ). FR4 board partially covered with copper pad (  $22~\text{mm}^2$  area,  $36~\mu\text{m}$  thickness ).
  - \*2 Mounted on FR4 board (  $25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$  ). FR4 board fully covered with copper pad (  $604 \text{ mm}^2$  area,  $36 \mu \text{m}$  thickness ).
  - \*3 Mounted on ceramic board ( 70 mm  $\times$  70 mm  $\times$  t1.0 mm ).

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#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

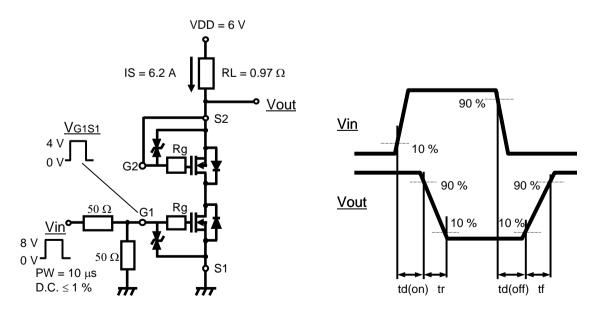
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1  mA, VGS = 0  V	12			V
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μΑ
Gate-source Leakage Current	IGSS1	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10	^
Gale-Source Leakage Current	IGSS2	$VGS = \pm 5 V$ , $VSS = 0 V$			±1.0	μΑ
Gate-source Threshold Voltage	Vth	IS = 0.56 mA, VSS = 6 V	0.35	0.9	1.4	V
	RSS(on)1	IS = 6.2 A, VGS = 4.5 V	1.6	2.2	2.9	
Source-source On-state Resistance	RSS(on)2	IS = 6.2 A, VGS = 3.8 V	1.8	2.5	3.3	<b>~</b> 0
Source-source On-state Resistance	RSS(on)3	IS = 6.2 A, VGS = 3.1 V	2.1	3.1	5.0	mΩ
	RSS(on)4	IS = 6.2 A, VGS = 2.5 V	2.6	4.3	8.5	
Body Diode Forward Voltage	VF(s-s)	IF = 6.2 A, VGS = 0 V		0.7	1.0	V
Input Capacitance *1	Ciss			2230		
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		410		pF
Reverse Transfer Capacitance *1	Crss			330		
Turn-on Delay Time *1,*2	td(on)	VDD = 6 V, VGS = 0 to 4 V		0.8		0
Rise Time *1,*2	tr	IS = 6.2 A		1.6		μS
Turn-off Delay Time *1,*2	td(off)	VDD = 6 V, VGS = 4 to 0 V		3.3		0
Fall Time *1,*2	tf	IS = 6.2 A		2.7		μS
Total Gate Charge *1	Qg	VDD = 6 V		17		
Gate-source Charge *1	Qgs	VGS = 0 to 4 V		7		nC
Gate-drain Charge *1	Qgd	IS = 12.4 A		4		
Gate Resistance *1	Rg	f = 1 MHz	400	700	1000	Ω

■ Electrostatic Discharge Characteristics Ta = 25 °C ± 3 °C

Standard	Test Type	Symbol	Conditions	Class*3	Value	Unit
 AEC-Q101-001	Human body model	HBM	$C = 100 \text{ pF}, R = 1.5 \text{ k}\Omega$	H2	$> 2k \text{ to } \leq 4k$	V

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- \*1 Guaranteed by design, not subject to production testing.
- \*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.
- \*3 AEC-Q101-001.

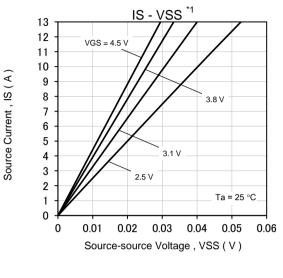


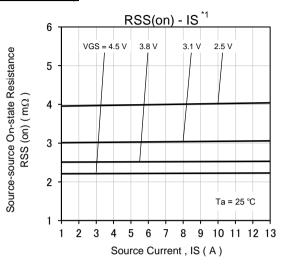
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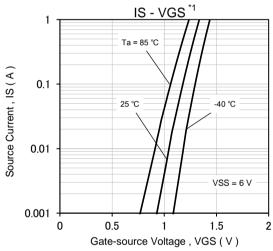
Established : 2019-11-08 Revised : ####-##-##

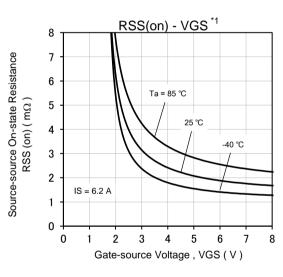
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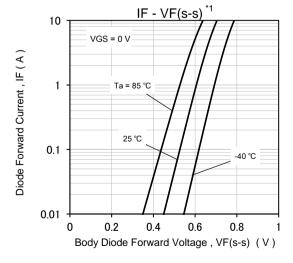
### Technical Data (reference)

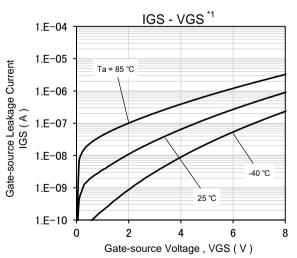












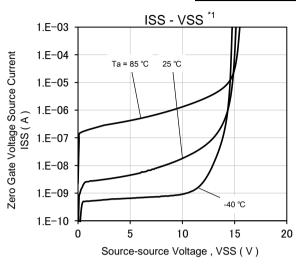
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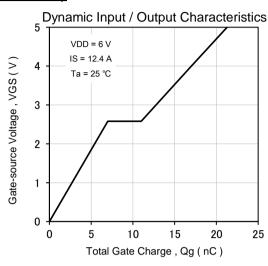
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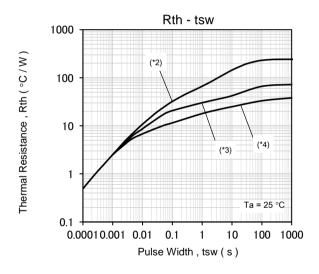
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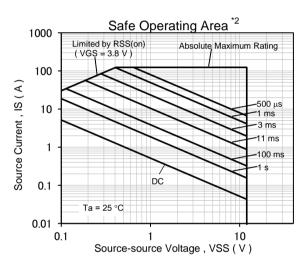
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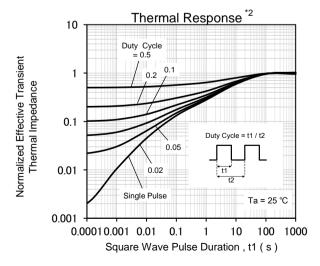
### Technical Data (reference)











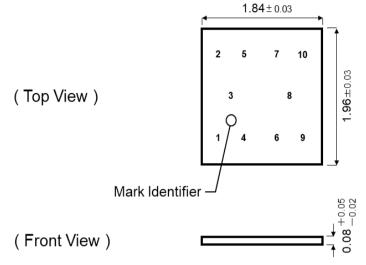
#### Note

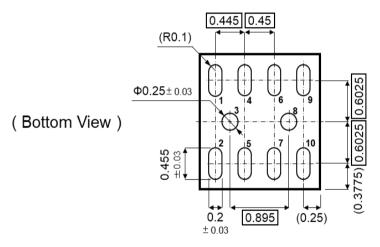
- \*1 Pulse measurement.
- \*2 Mounted on FR4 board (  $25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$  ). FR4 board partially covered with copper pad (  $22 \text{ mm}^2$  area,  $36 \mu \text{m}$  thickness ).
- $^*3$  Mounted on FR4 board ( 25.4 mm  $\times$  25.4 mm  $\times$  t1.0 mm ). FR4 board fully covered with copper pad ( 604 mm² area, 36  $\mu m$  thickness ).
- \*4 Mounted on ceramic board ( 70 mm  $\times$  70 mm  $\times$  t1.0 mm ).

# **Panasonic**

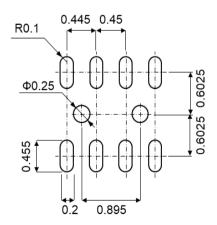
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■ Outline Unit: mm





### ■ Land & Stencil Pattern (reference)



Unit: mm

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Established : 2019-11-08 Revised : ####-##-## Doc No. TD4-ZZ-01773 Revision. 0

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MOS FET FCAB21830L

# **Datasheet Amendment History**

Version	Status	Date	Change point(s)
-	Formal	2019.10.01	

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